

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
150V	3.8mΩ@10V	235A



合肥矽普半导体

Siliup Semiconductor Technology Co., Ltd

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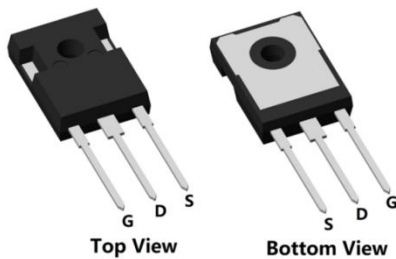
Feature

- Fast Switching
- Low Gate Charge and Rdson
- Advanced Split Gate Trench Technology
- 100% Single Pulse avalanche energy Test

Applications

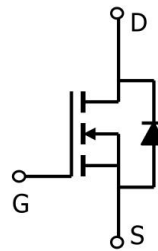
- PWM Application
- Hard switched and high frequency circuits
- Power Management

Package

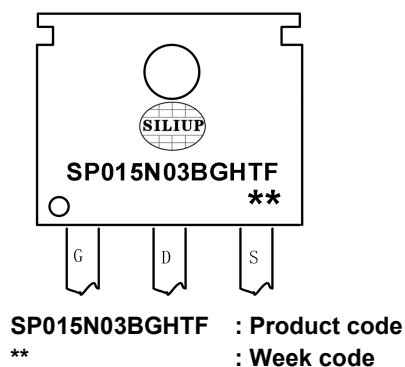


TO-247(1:G 2:D 3:S)

Circuit diagram



Marking



Order Information

Device	Package	Unit/Tube
SP015N03BGHTF	TO-247	30

Absolute maximum ratings (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	150	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current (Tc=25°C)	I_D	235	A
Continuous Drain Current (Tc=100°C)	I_D	160	A
Pulsed Drain Current	I_{DM}	940	A
Single Pulse Avalanche Energy ¹	E_{AS}	1681	mJ
Power Dissipation (Tc=25°C)	P_D	430	W
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	0.29	°C/W
Storage Temperature Range	T_{STG}	-55 to 150	°C
Operating Junction Temperature Range	T_J	-55 to 150	°C

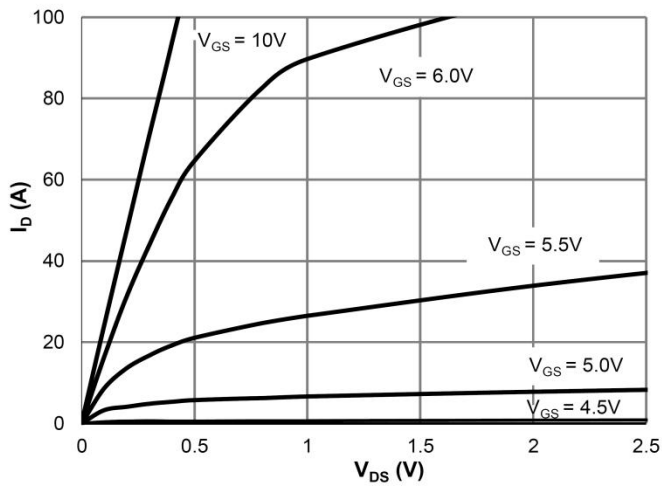
Electrical characteristics (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	ID = 250μA, VGS = 0V	150	-	-	V
Drain-Source Leakage Current	IDSS	VDS = 80V, VGS = 0V	-	-	1	uA
Gate-Source Leakage Current	IGSS	VGS = ±20V, VDS = 0V	-	-	±100	nA
Gate Threshold Voltage	VGS(th)	VDS = VGS, ID = 250μA	2.5	3.5	4.5	V
Static Drain-Source On-Resistance	RDS(ON)	VGS = 10V, ID = 20A	-	3.8	4.3	mΩ
Dynamic characteristics						
Input Capacitance	Ciss	VDS=75V , VGS=0V , f=1MHz	-	10402	-	pF
Output Capacitance	Coss		-	635	-	
Reverse Transfer Capacitance	Crss		-	24	-	
Total Gate Charge	Qg	VDS=75V , VGS=10V , ID=20A	-	148	-	nC
Gate-Source Charge	Qgs		-	58	-	
Gate-Drain Charge	Qgd		-	40	-	
Switching Characteristics						
Turn-On Delay Time	Td(on)	VDD=75V, VGS=10V , RG=3.0Ω, ID=20A	-	40	-	nS
Rise Time	Tr		-	72	-	
Turn-Off Delay Time	Td(off)		-	108	-	
Fall Time	Tf		-	58	-	
Diode Characteristics						
Diode Forward Voltage	VSD	VGS=0V , IS=1A , TJ=25℃	-	-	1.2	V
Maximum Body-Diode Continuous Current	IS		-	-	235	A
Reverse Recovery Time	Trr	IS=15A, di/dt=100A/us, TJ=25℃	-	112	-	nS
Reverse Recovery Charge	Qrr		-	426	-	nC

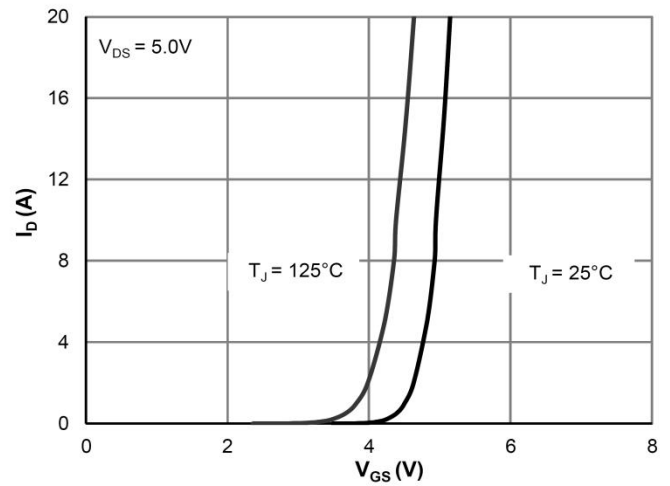
Note :

1. The test condition is $V_{DD}=50V, V_{GS}=10V, L=0.5mH, R_G=25\Omega$

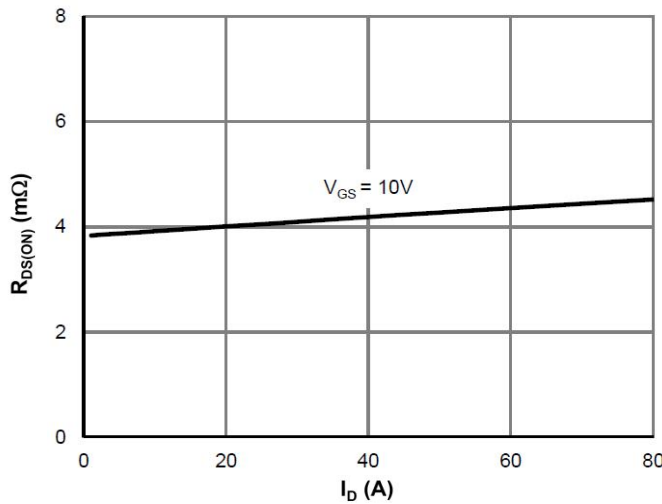
Typical Characteristics



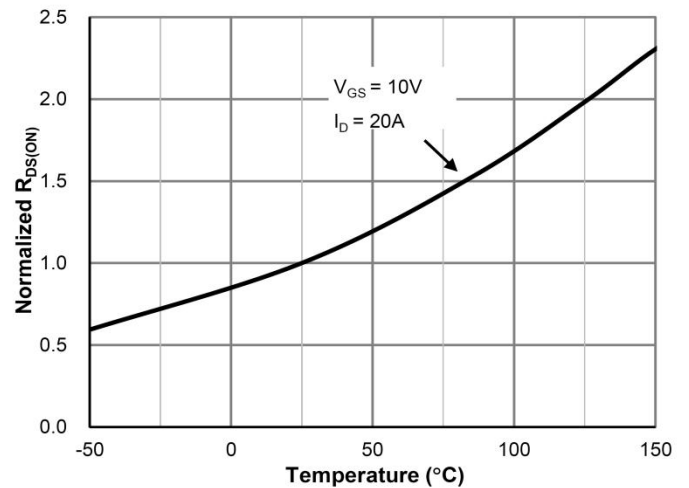
Saturation Characteristics



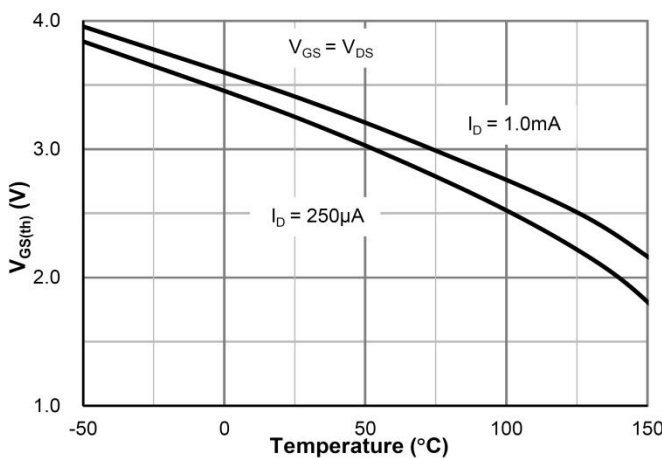
Transfer Characteristics



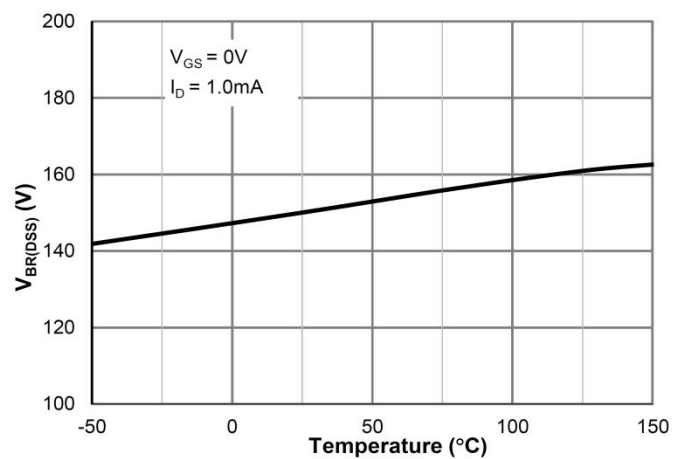
$R_{DS(ON)}$ vs. Drain Current



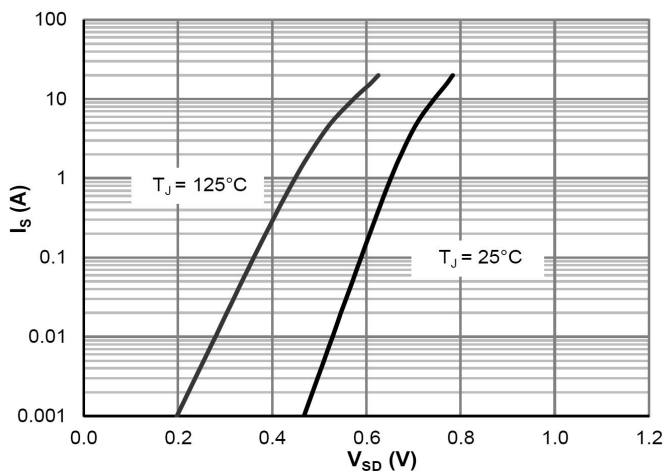
$R_{DS(ON)}$ vs. Junction Temperature



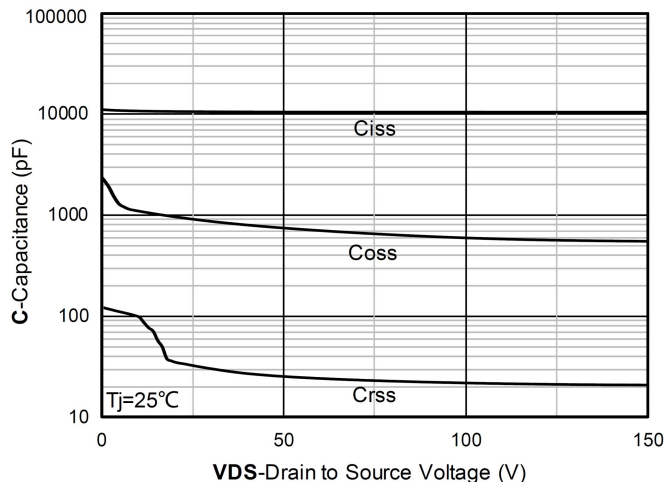
$V_{GS(th)}$ vs. Junction Temperature



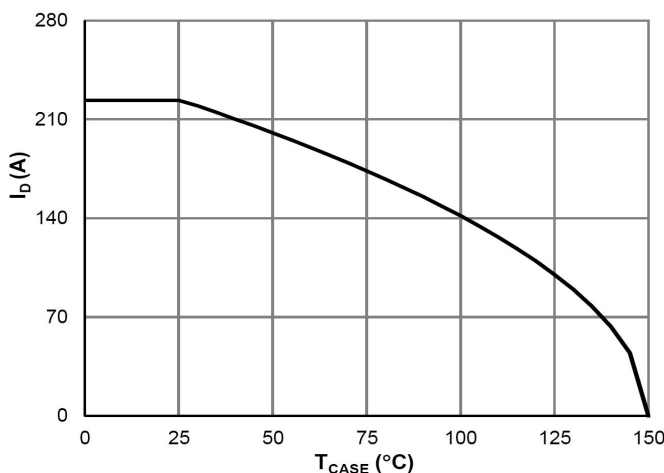
$V_{BR(DSS)}$ vs. Junction Temperature



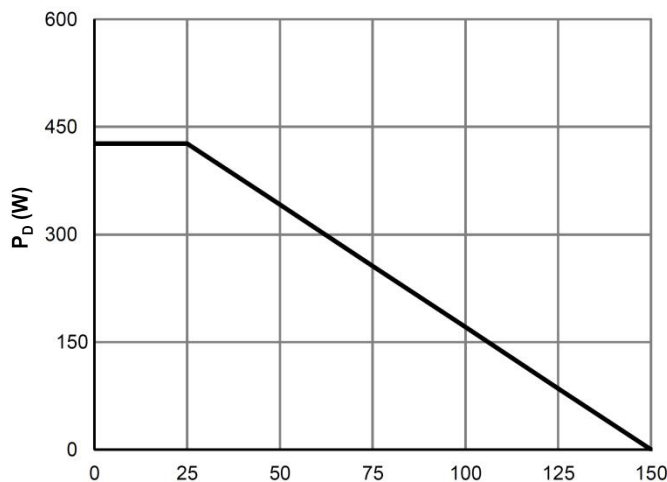
Body-Diode Characteristics



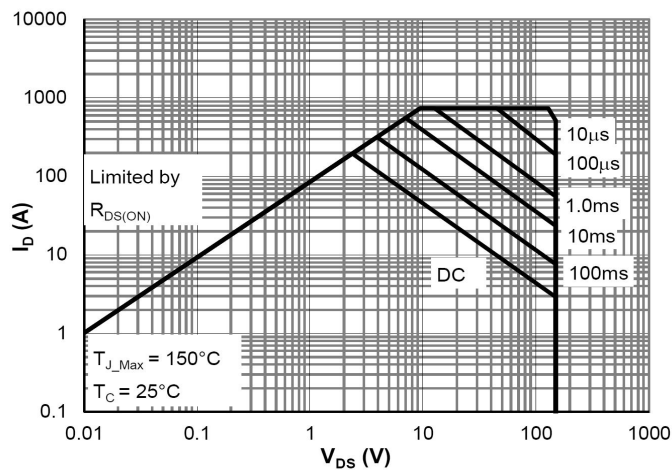
Capacitance Characteristics



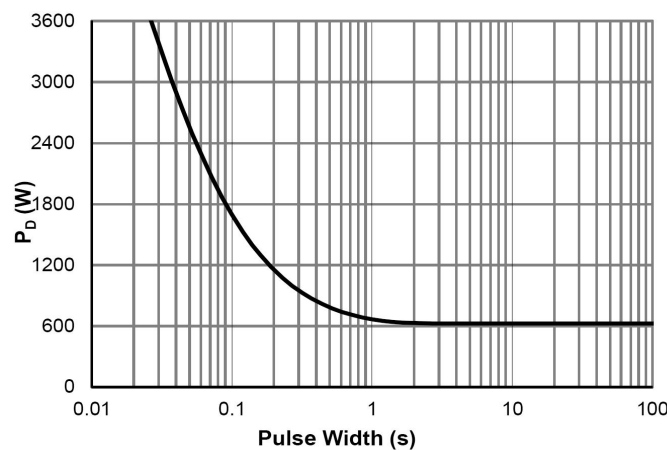
Current De-rating



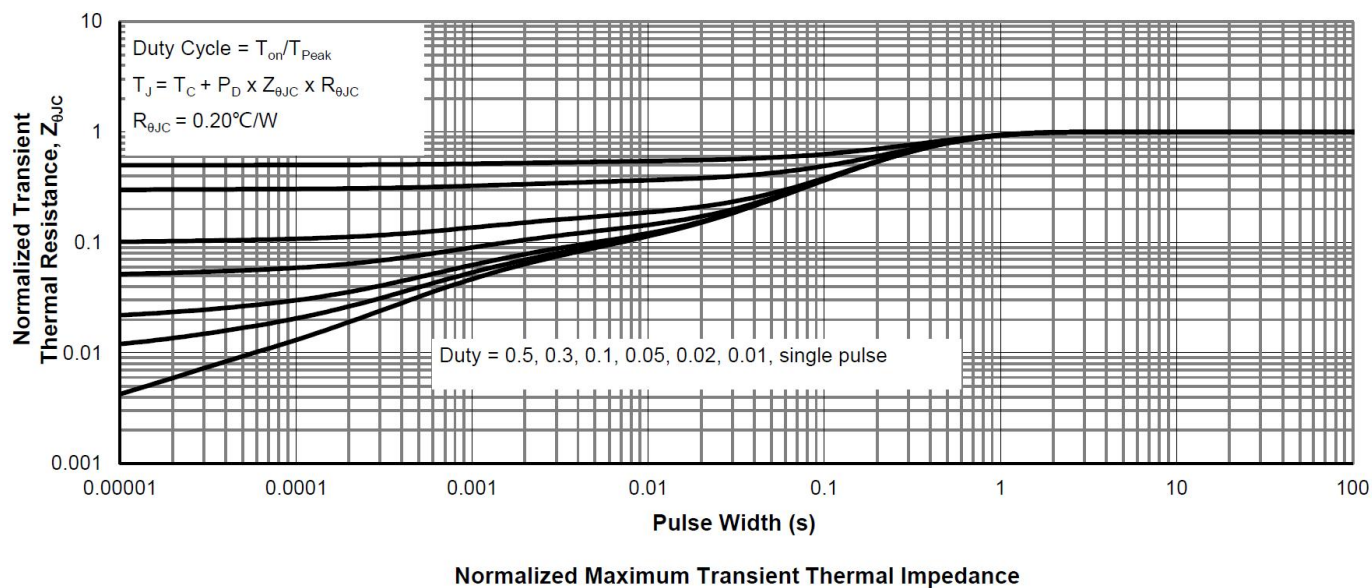
Power De-rating

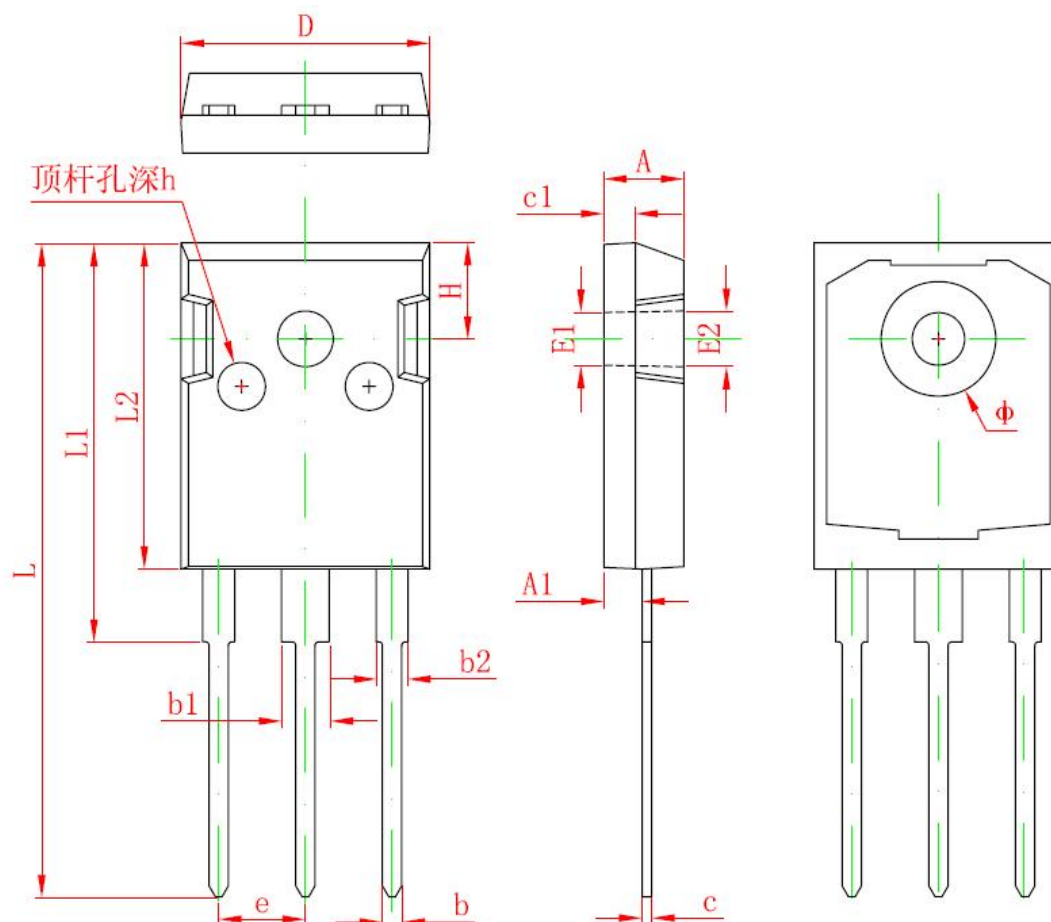


Maximum Safe Operating Area



Single Pulse Power Rating, Junction-to-Case



TO-247 Package Information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.850	5.150	0.191	0.200
A1	2.200	2.600	0.087	0.102
b	1.000	1.400	0.039	0.055
b1	2.800	3.200	0.110	0.126
b2	1.800	2.200	0.071	0.087
c	0.500	0.700	0.020	0.028
c1	1.900	2.100	0.075	0.083
D	15.450	15.750	0.608	0.620
E1	3.500 REF.		0.138 REF.	
E2	3.600 REF.		0.142 REF.	
L	40.900	41.300	1.610	1.626
L1	24.800	25.100	0.976	0.988
L2	20.300	20.600	0.799	0.811
Φ	7.100	7.300	0.280	0.287
e	5.450 TYP.		0.215 TYP.	
H	5.980 REF.		0.235 REF.	
h	0.000	0.300	0.000	0.012